

## Electrical Specifications

### ABSOLUTE MAXIMUM CONDITIONS

Symbol	Parameter	Min	Typ	Max	Units
$P_D$	Power Dissipation	–	–	1	W
$V_{CC}$	Supply Voltage	–0.5	–	7.0	V
$V_I$	Input Voltage	–0.5	–	$V_{CC}+0.5$	V
$V_O$	Output Voltage	–0.5	–	$V_{CC}+0.5$	V
$T_{OP}$	Operating Temperature (Ambient)	–25	–	85	°C
$T_{STG}$	Storage Temperature	–40	–	125	°C

Note: Permanent device damage may occur if Absolute Maximum Ratings are exceeded.  
Functional operation should be restricted to the conditions described under Normal Operating Conditions.

### NORMAL OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Units
$V_{CC}$	Supply Voltage (5V ±10%)	4.5	5	5.5	V
$T_A$	Ambient Temperature	0	–	70	°C

### DAC CHARACTERISTICS

(Under Normal Operating Conditions Unless Noted Otherwise)

Symbol	Parameter	Notes	Min	Typ	Max	Units
$f_{MAX}$	Clock Rate		–	–	85	MHz
	DAC-to-DAC Correlation	See Note 1	–	–	5	%
	DAC-to-DAC Crosstalk		–	TBD	–	dB
	Output Skew	See Note 2	–	–	2	ns
	Output Settling Time	See Note 3	–	13	–	ns
	Output Rise / Fall Time	10% to 90%	–	–	5	ns
	Comparator Sensitivity		–	50	–	mV
	Output Current	See Note 4				
	White referenced to Black		–	–	30	mA
	Black referenced to Blank		–	–	50	μA
	Blank Level		0	–	50	μA

Note: Monotonicity is guaranteed by design.  
Unless otherwise specified, Analog Output Load = 50Ω, 30pF.

Note 1: Correlation is measured about the midpoint of the Red, Green, and Blue DAC outputs at full scale.

Note 2: Measured from the 50% point of the Red, Green, and Blue DAC outputs when switching from black level to full scale.

Note 3: Settling time is measured from 50% of the full scale transition to the output remaining within ±1 LSB of the final value.

Note 4: Measured with RSET = 383Ω, LOAD = 50Ω, ≤10pF.

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**DC CHARACTERISTICS**

(Under Normal Operating Conditions Unless Noted Otherwise)

Symbol	Parameter	Notes	Min	Typ	Max	Units
$I_{CCDE}$	Power Supply Current	0°C, 5.5V, 72 MHz MCLK	–	150	170	mA
$I_{IL}$	Input Leakage Current		–100	–	+100	μA
$I_{OZ}$	Output Leakage Current	High Impedance	–100	–	+100	μA
$V_{IL}$	Input Low Voltage	All input pins	–0.5	–	0.8	V
$V_{IH}$	Input High Voltage	All input pins except clocks	2.0	–	$V_{CC}+0.5$	V
		LCLK, (MCLK, VCLK if external)	2.8	–	$V_{CC}+0.5$	V
$V_{OL}$	Output Low Voltage	Under max load per table below (5V)	–	–	0.5	V
$V_{OH}$	Output High Voltage	Under max load per table below (5V)	$V_{CC}-0.5$	–	–	V
ESR	Equivalent Series Resistance	XTAL In, XTAL Out Crystal Oscillator	–	–	100	Ω

**DC DRIVE CHARACTERISTICS**

(Under Normal Operating Conditions Unless Noted Otherwise)

Symbol	Parameter	Output Pins	DC Test Conditions	Min	Units
$I_{OL}$	Output Low Drive	HSYNC, VSYNC, LRDY#, IRQ9, IOCS16#	$V_{OUT}=V_{OL}, V_{CC}=5V$	-12	mA
		MEMCS16#, ZWS#, WE#, OE#, CASxxx#	$V_{OUT}=V_{OL}, V_{CC}=5V$	-12	mA
		MA4:1, XA4:1	$V_{OUT}=V_{OL}, V_{CC}=5V$	-16	mA
		PCLK, RASx#, MA8:5, MA0, D31:0, AEN, LDEV#	$V_{OUT}=V_{OL}, V_{CC}=5V$	-8	mA
		MCLK	$V_{OUT}=V_{OL}, V_{CC}=5V$	-2	mA
		XTALO	$V_{OUT}=V_{OL}, V_{CC}=5V$	-1	mA
		All other outputs	$V_{OUT}=V_{OL}, V_{CC}=5V$	-4	mA
$I_{OH}$	Output High Drive	HSYNC, VSYNC, LRDY#, IRQ9, IOCS16#	$V_{OUT}=V_{OH}, V_{CC}=5V$	12	mA
		MEMCS16#, ZWS#, WE#, OE#, CASxxx#	$V_{OUT}=V_{OH}, V_{CC}=5V$	12	mA
		MA4:1, XA4:1	$V_{OUT}=V_{OH}, V_{CC}=5V$	16	mA
		PCLK, RASx#, MA8:5, MA0, D31:0, AEN, LDEV#	$V_{OUT}=V_{OH}, V_{CC}=5V$	8	mA
		MCLK	$V_{OUT}=V_{OH}, V_{CC}=5V$	2	mA
		XTALO	$V_{OUT}=V_{OH}, V_{CC}=5V$	1	mA
		All other outputs	$V_{OUT}=V_{OH}, V_{CC}=5V$	4	mA

**AC TEST CONDITIONS**

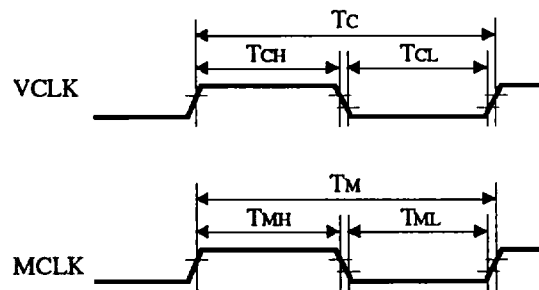
(Under Normal Operating Conditions Unless Noted Otherwise)

Output Pins	Output	Output	Capacitive
	Low Voltage	High Voltage	Load
All Outputs (except XTALO)	$V_{OL}$	2.4V	50pF

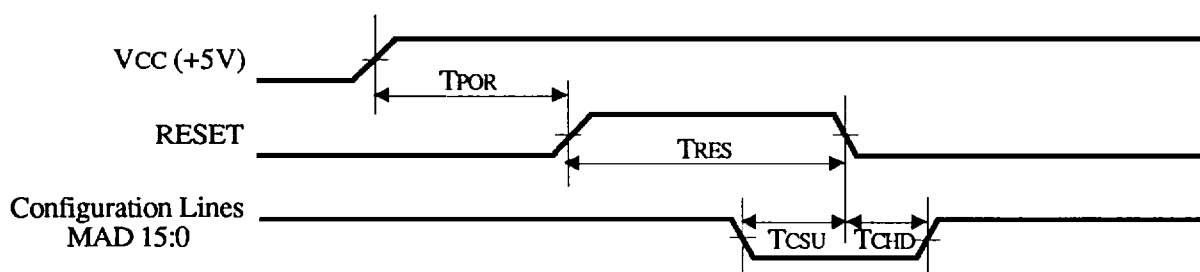
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**AC TIMING CHARACTERISTICS - EXTERNAL CLOCK TIMING**

Symbol	Parameter	Notes	Min	Typ	Max	Units
$T_C$	CLK Period	65 MHz external VCLK	15.38	–	–	ns
$T_{CH}$	CLK High Time		$0.45T_C$	–	$0.55T_C$	ns
$T_{CL}$	CLK Low Time		$0.45T_C$	–	$0.55T_C$	ns
$T_M$	MCLK Period	65 MHz external MCLK	15.38	–	–	ns
$T_{MH}$	MCLK High Time		$0.45T_M$	–	$0.55T_M$	ns
$T_{ML}$	MCLK Low Time		$0.45T_M$	–	$0.55T_M$	ns
$T_{RF}$	Clock Rise / Fall		–	–	4	ns
$T_{REF}$	Reference Clock Period	Reference clock for internal synthesizer	50	69.8	100	ns


**External Clock Timing**
**AC TIMING CHARACTERISTICS - RESET TIMING**

Symbol	Parameter	Notes	Min	Typ	Max	Units
$T_{RES}$	RESET Pulse Width		$64T_M$	–	–	ns
$T_{CSU}$	Configuration setup time		20	–	–	ns
$T_{CHD}$	Configuration hold time		5	–	–	ns
$T_{POR}$	Power on to RESET active delay		–	–	1	s


**Reset Timing**

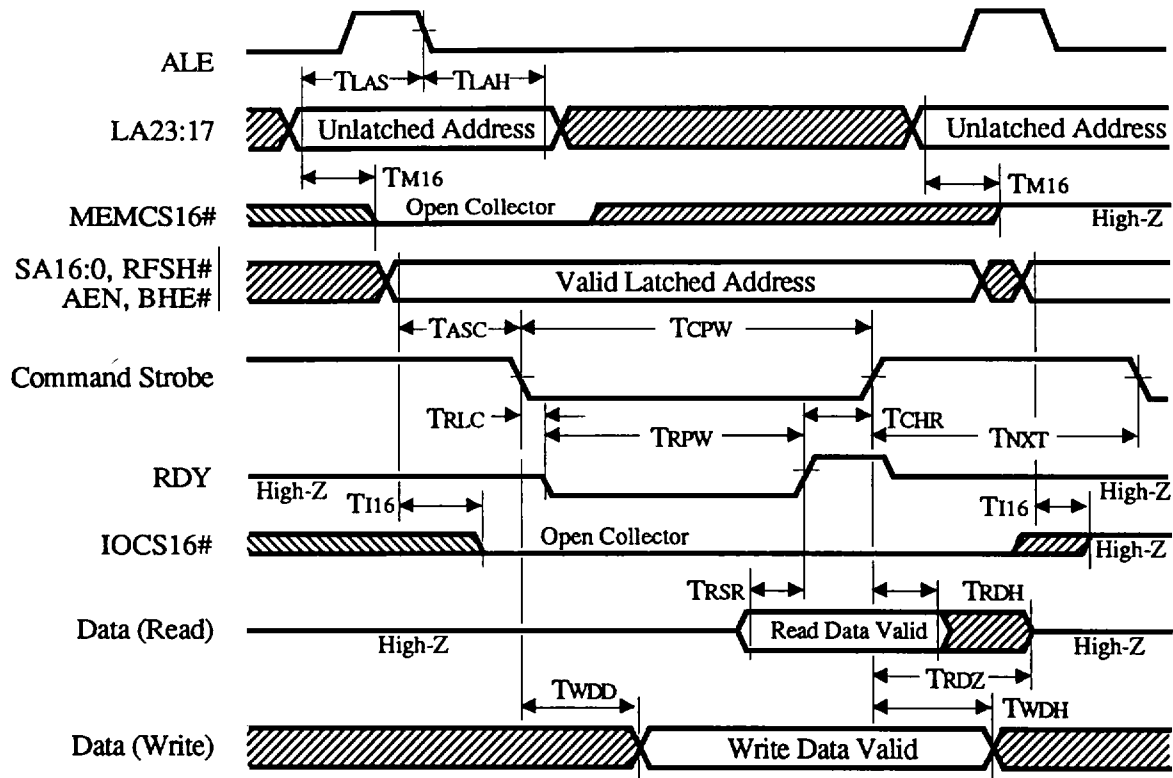
**Note:** Electrical specifications contained herein are preliminary and subject to change without notice.

## AC TIMING CHARACTERISTICS - ISA BUS TIMING

Symbol	Parameter	Notes	Min	Typ	Max	Units
$T_{ASC}$	Address Setup to Command Strobe		30	–	–	ns
$T_{LAS}$	LA Address Setup to ALE Inactive		10	–	–	ns
$T_{LAH}$	LA Address Hold from ALE Inactive		10	–	–	ns
$T_{CPW}$	Command Strobe Pulse Width		60	–	–	ns
$T_{CHR}$	Command Strobe Hold from RDY high		30	–	–	ns
$T_{NXT}$	Command Strobe Inactive to Next Strobe	See Note 1	$3T_M$	–	–	ns
$T_{M16}$	MEMCS16# Delay from valid unlatched address		–	–	20	ns
$T_{I16}$	IOCS16# Delay from valid address		–	–	20	ns
$T_{RLC}$	RDY Active Low Delay from Command Strobe		–	–	30	ns
$T_{RPW}$	RDY Pulse Width		0	–	$100T_M$	ns
$T_{RSR}$	Read Data Setup to Ready		-25	–	–	ns
$T_{RDH}$	Read Data Hold from Command Strobe Inactive		10	–	–	ns
$T_{RDZ}$	Read Data Tristate from Command Strobe Inactive		–	–	40	ns
$T_{WDD}$	Write Data Delay from Command Strobe Active		–	–	$T_{CPW}-15$	ns
$T_{WDH}$	Write Data Hold from Command Strobe Inactive		10	–	–	ns

Note 1: This becomes  $6T_M$  if host clock=MCLK/2. See XR01[3].

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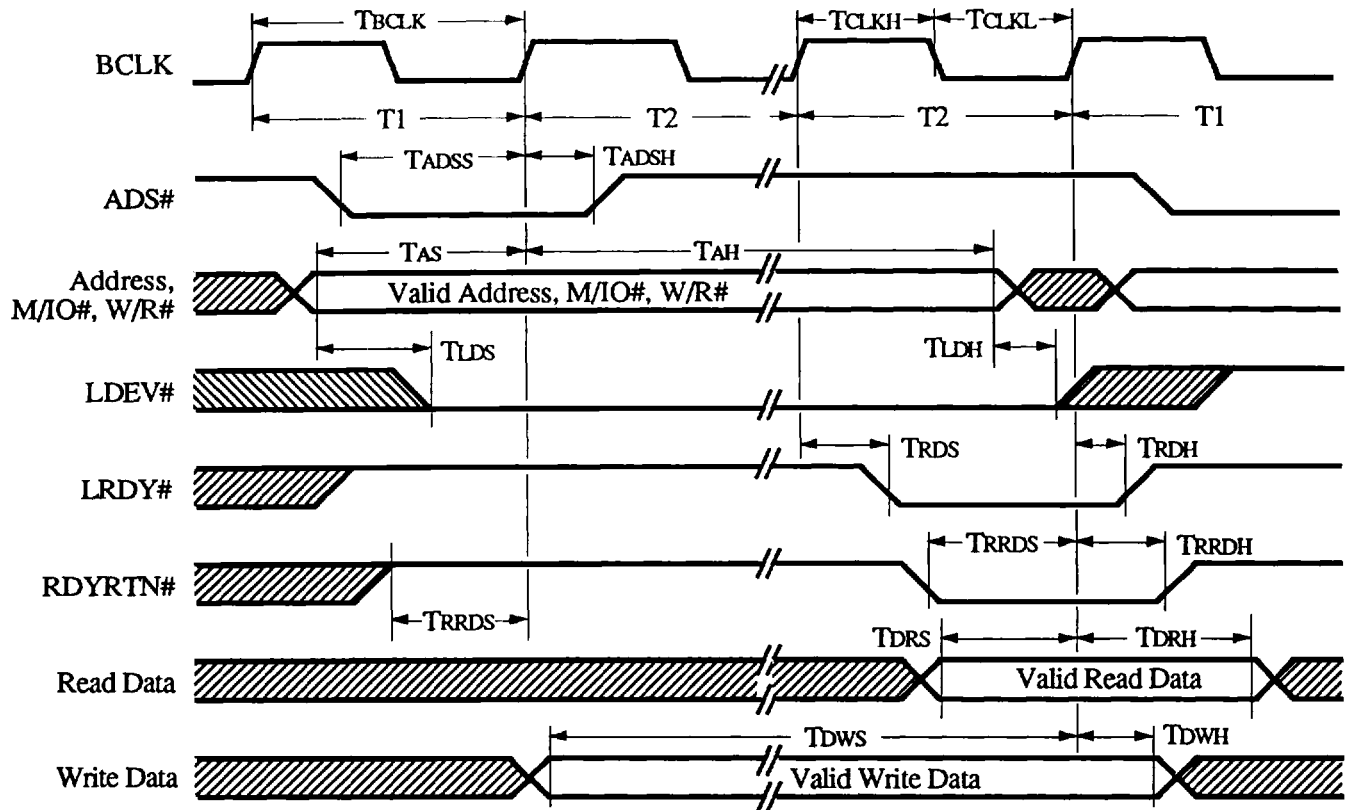
ISA Bus Cycle Timing

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## DC TIMING CHARACTERISTICS - 486 LOCAL BUS TIMING

Symbol	Parameter	Notes	Min	Typ	Max	Units
T <sub>BCLK</sub>	Local Bus Clock Cycle Time	50MHz	20			ns
T <sub>CLKL</sub>	Local Bus Clock Low Time	Duty Cycle 45/55	9	10	11	ns
T <sub>CLKH</sub>	Local Bus Clock High Time	Duty Cycle 45/55	9	10	11	ns
T <sub>LDS</sub>	Delay from Address Valid to LDEV#		0	–	20	ns
T <sub>LDH</sub>	LDEV# Inactive from Address Not Valid		0	–	20	ns
T <sub>ADSS</sub>	ADS# Setup to BCLK rising edge		4	–	–	ns
T <sub>ADSH</sub>	ADS# Hold from BCLK rising edge		5	–	–	ns
T <sub>AS</sub>	Address, M/IO#, R/W# Setup to End of T1		4	–	–	ns
T <sub>AH</sub>	Address, M/IO#, R/W# Hold from End of T1		T <sub>CLKH</sub> +8	–	–	ns
T <sub>RDS</sub>	LRDY# Setup Time from Start of final T2		18	–	–	ns
T <sub>RDH</sub>	LRDY# Hold Time from End of T2		0	–	15	ns
T <sub>RRDS</sub>	RDYRTN# Setup Time to End of final T2		18	–	–	ns
T <sub>RRDH</sub>	RDYRTN# Hold Time from End of final T2		0	–	15	ns
T <sub>DRS</sub>	Read Data Setup Time to End of final T2		18	–	–	ns
T <sub>DRH</sub>	Read Data hold Time from End of final T2		0	–	15	ns
T <sub>DWS</sub>	Write Data Setup Time to End of first T2		18	–	–	ns
T <sub>DWH</sub>	Write Data hold Time from End of final T2		0	–	15	ns

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64300 / 301 VL Bus (486 Local Bus) Timing

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## AC TIMING CHARACTERISTICS - DRAM READ/WRITE TIMING

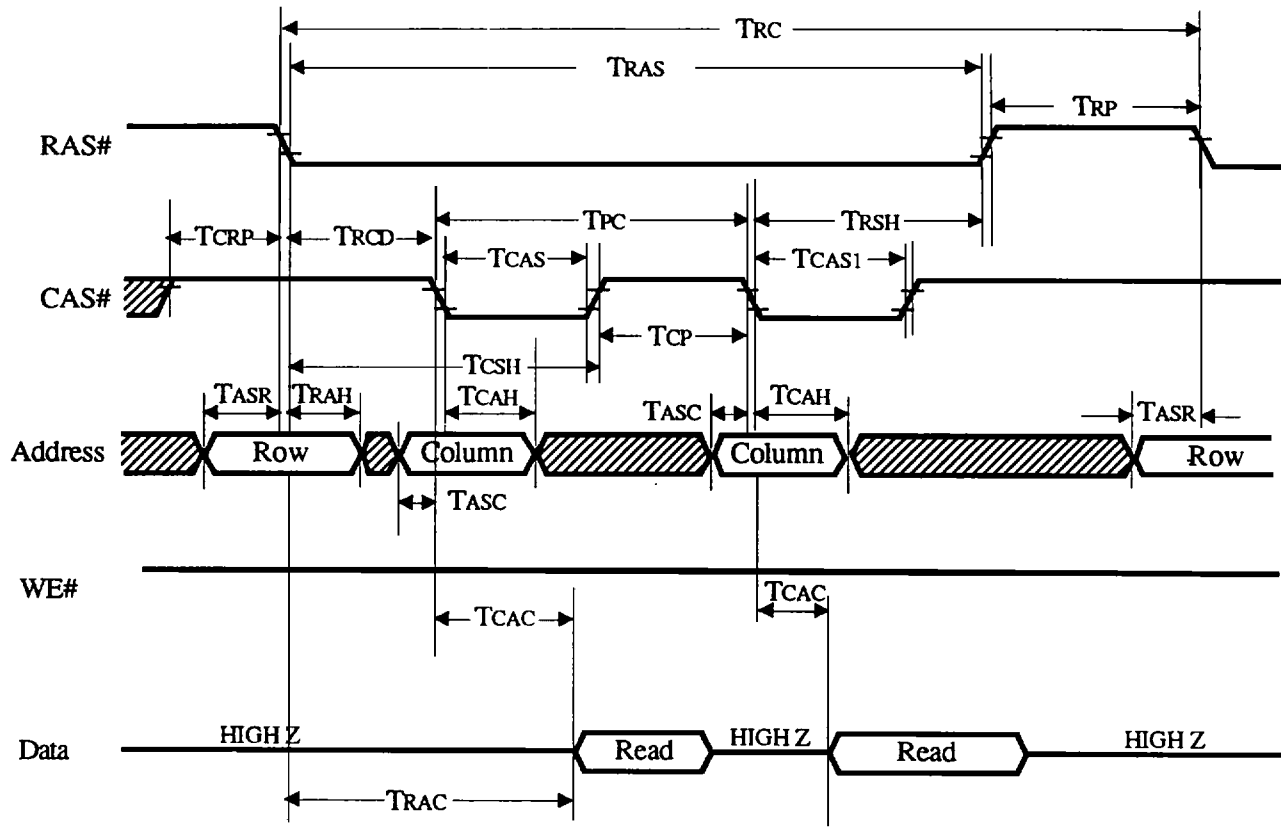
				MCLK Frequency (MHz)			
				72.0	64.3	52.9	
				DRAM Access Time			
Symbol	Parameter	Min	Max	-6	-7	-8	Units
$T_{RC}$	Read/Write Cycle Time	$9T_M-5$	–	<b>120.0</b>	135.1	165.1	ns
$T_{RAS}$	RAS# Pulse Width (Min)	$5T_M-5$	<b>See Note 1</b>	64.4	72.8	89.5	ns
$T_{RP}$	RAS# Precharge	$4T_M-5$	–	50.6	57.3	70.6	ns
$T_{CRP}$	CAS# to RAS# precharge	$4T_M-7$	–	48.6	55.3	68.6	ns
$T_{CSH}$	CAS# Hold from RAS#	$5T_M-5$	–	63.4	72.8	88.5	ns
$T_{RCD}$	RAS# to CAS# delay	$3T_M-5$		36.7	41.7	51.7	ns
			$3T_M+5$	46.7	51.7	61.7	ns
$T_{RSH}$	RAS# Hold from CAS#	$2T_M-5$	–	22.8	26.1	32.8	ns
$T_{CP}$	CAS# Precharge	$T_M-3.9$	–	<b>10.0</b>	11.7	15.0	ns
$T_{CAS}$	CAS# Pulse Width	$2T_M-5$	–	22.8	26.1	32.8	ns
$T_{WP}$	WE# Pulse Width	$2T_M-5$	–	22.8	26.1	32.8	ns
$T_{CAS1}$	CAS# Pulse Width (Fast Page Cycle)	$2T_M-5$	–	22.8	26.1	32.8	ns
$T_{ASR}$	Row Address Setup to RAS#	$(3T_M/2)-15$	–	5.8	8.3	13.4	ns
$T_{ASC}$	Column Address Setup to CAS#	$(3T_M/2)-15$	–	5.8	8.3	13.4	ns
$T_{RAH}$	Row Address Hold from RAS#	$T_M-3.9$	–	<b>10.0</b>	11.7	15.0	ns
$T_{CAH}$	Column Address Hold from CAS#	$(3T_M/2)-5.8$	–	<b>15.0</b>	17.5	22.6	ns
$T_{CAC}$	Data Access Time from CAS#	–	$2T_M-7.8$	<b>20.0</b>	23.3	30.0	ns
$T_{AA}$	Data Access Time from Column Address	–	$3T_M-11.7$	<b>30.0</b>	<b>35.0</b>	<b>45.0</b>	ns
$T_{RAC}$	Data Access time from RAS#	–	$5T_M-5$	64.4	72.8	89.5	ns
$T_{DS}$	Write Data Setup to CAS#	$T_M-7$	–	6.9	8.6	11.9	ns
$T_{DH}$	Write Data Hold from CAS#	$(3T_M/2)-5.8$	–	<b>15.0</b>	17.5	22.6	ns
$T_{DS}$	Write Data Setup to WE#	$T_M-7$	–	6.9	8.6	11.9	ns
$T_{DH}$	Write Data Hold from WE#	$(3T_M/2)-5.8$	–	<b>15.0</b>	17.5	22.6	ns
$T_{PC}$	CAS# Cycle Time	$3T_M-1.7$	–	<b>40.0</b>	<b>45.0</b>	55.0	ns

Note: Parameters printed in bold are the limiting cases for industry standard DRAM specifications.

Note 1: Maximum RAS pulse width may be as high as  $2+(256*3)$  memory clock cycles =  $770T_M$  if the BitBlit Engine is given full memory bandwidth. This depends on other events which have higher priority including refresh cycles and display update.

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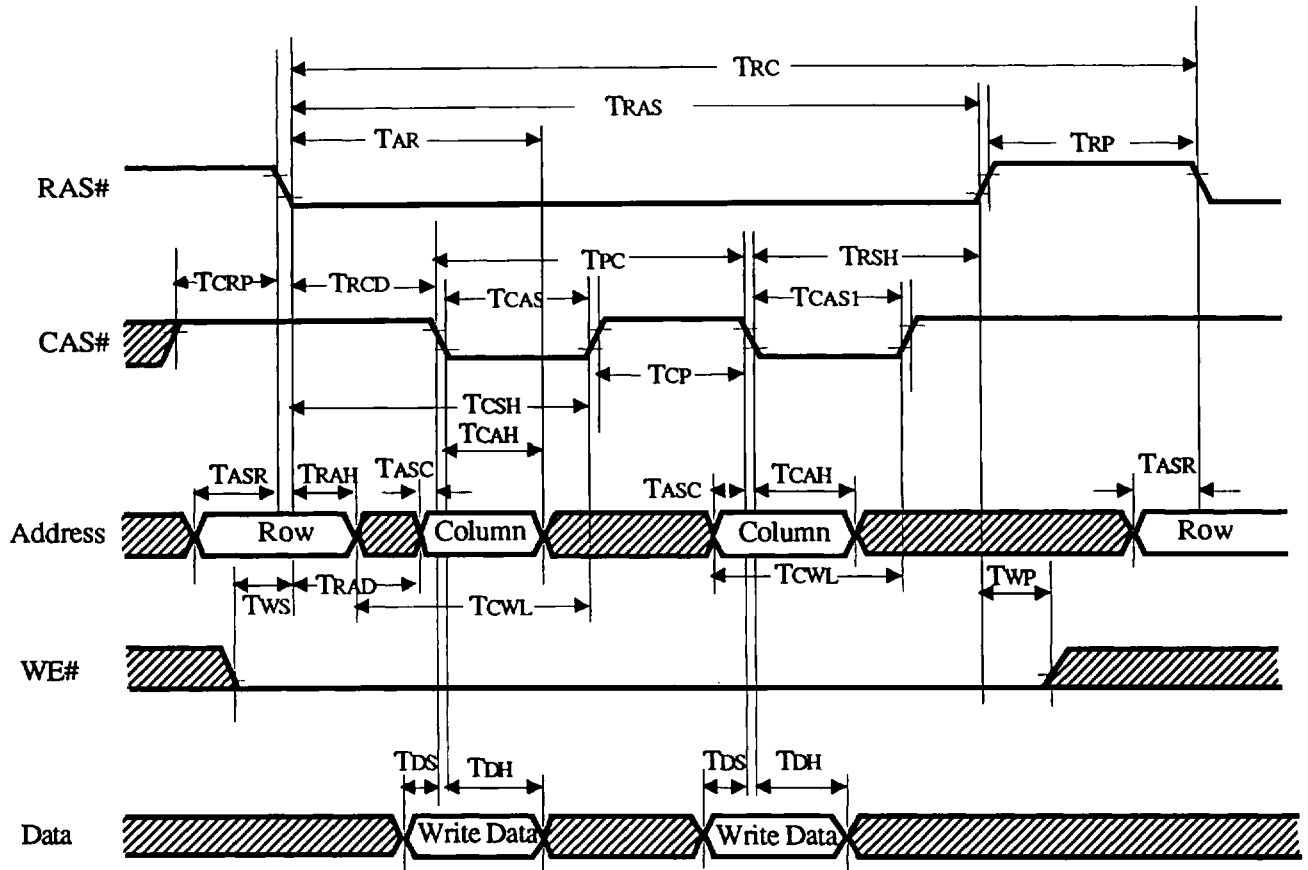




**DRAM Page Mode Read Cycle Timing**

**Note:** The above diagram represents a typical page mode read cycle. The number of actual CAS cycles may vary.

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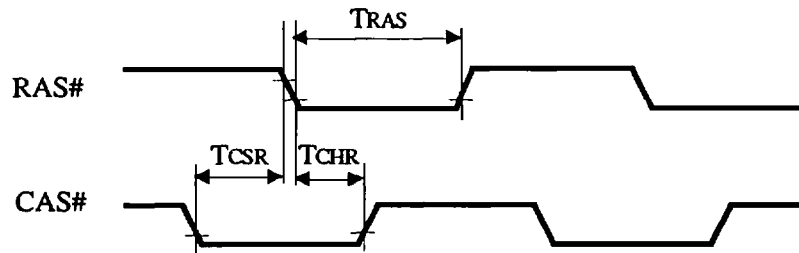
**DRAM Page Mode Write Cycle Timing**

Note: The above diagram represents a typical page mode write cycle.

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**AC TIMING CHARACTERISTICS - REFRESH TIMING**

				MCLK Frequency (MHz)			
				72.0	64.3	52.9	
				DRAM Access Time			
Symbol	Parameter	Min	Max	-6	-7	-8	Units
T <sub>CHR</sub>	RAS to CAS delay	5T <sub>M</sub> -6	-	63.4	71.8	88.5	ns
T <sub>CSR</sub>	CAS to RAS delay	2T <sub>M</sub> -7.5	-	20.3	23.6	30.3	ns
TRAS	RAS pulse width	5T <sub>M</sub> -5	-	64.4	72.8	89.5	ns



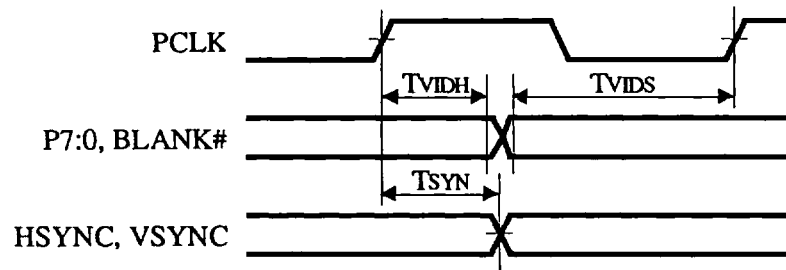
**CAS-Before-RAS (CBR) DRAM Refresh Cycle Timing**

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**AC TIMING CHARACTERISTICS - CRT VIDEO TIMING**

Symbol	Parameter	Notes	Min	Typ	Max	Units
$T_{VIDS}$	PCLK Setup to P7:0, BLANK#	PCLK = 45MHz	3	–	19.2	ns
$T_{VIDH}$	PCLK Hold from P7:0, BLANK#	PCLK = 45MHz	3	–	19.2	ns
$T_{SYN}$	HSYNC, VSYNC delay from PCLK		–	–	40	ns

Note: Output load on PCLK, P7:0, and BLANK# = 30pF

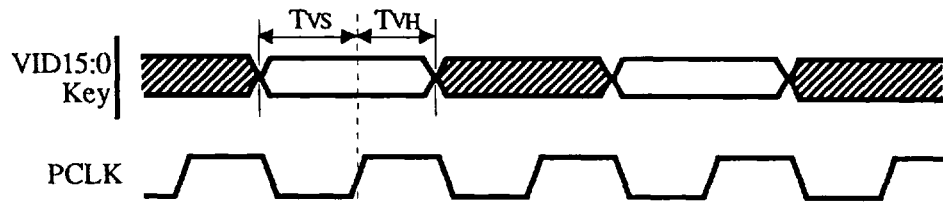


**CRT Video Data and Control Signal Timing**

**AC TIMING CHARACTERISTICS - VIDEO OVERLAY INPUT TIMING**

Symbol	Parameter	Notes	Min	Typ	Max	Units
$T_{VS}$	KEY, VID15:0 Setup to PCLK rising edge		15	–	–	ns
$T_{VH}$	KEY, VID15:0 Hold from PCLK rising edge		0	–	–	ns

Note: Output load on PCLK = 30pF



**Video Overlay Timing**

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